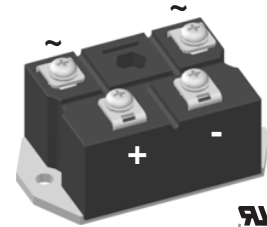
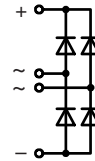


Single Phase Rectifier Bridge

 $I_{dAV} = 52/72 \text{ A}$
 $V_{RRM} = 800-1800 \text{ V}$

V_{RSM}	V_{RRM}	Type	
V	V		
900	800	VBO 52-08NO7	VBO 72-08NO7
1300	1200	VBO 52-12NO7	VBO 72-12NO7
1700	1600	VBO 52-16NO7	VBO 72-16NO7
1900	1800	VBO 52-18NO7	VBO 72-18NO7



Symbol	Conditions	Maximum Ratings	
		VBO 52	VBO 72
I_{dAV}	$T_C = 100^\circ\text{C}$, module	52	72 A
I_{dAV}	$T_A = 45^\circ\text{C}$ ($R_{thCA} = 0.6 \text{ K/W}$), module	41	49 A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	550 600 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	500 550 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1520 1520 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1250 1250 A ² s
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	2500 V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3000 V~
M_d	Mounting torque (M5)	$5 \pm 15\%$	Nm
	Terminal connection torque (M5)	$5 \pm 15\%$	Nm
Weight	typ.	160	g

Features

- Package with screw terminals
- Isolation voltage 3000 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- UL registered E 72873

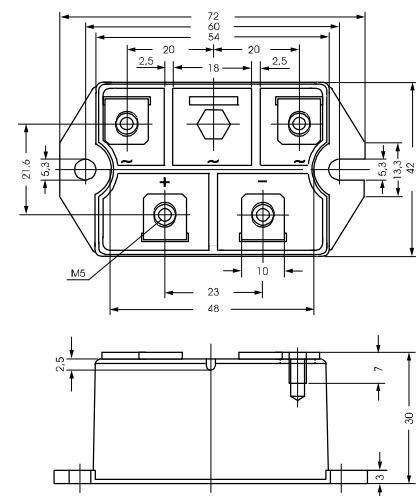
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature & power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Conditions	Characteristic Values	
		VBO 52	VBO 72
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$	≤ 0.3	0.3 mA
	$V_R = V_{RRM}$; $T_{VJ} = T_{VJM}$	≤ 5	5 mA
V_F	$I_F = 150 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	≤ 1.8	1.6 V
V_{TO}	For power-loss calculations only	0.8	0.8 V
r_T	$T_{VJ} = T_{VJM}$	8	5 m Ω
R_{thJC}	per diode	1.45	1.1 K/W
	per module	0.36	0.28 K/W
R_{thJK}	per diode	1.87	1.52 K/W
	per module	0.47	0.38 K/W
d_s	Creeping distance on surface	10	mm
d_A	Creepage distance in air	9.4	mm
a	Max. allowable acceleration	50	m/s ²

Data according to IEC 60747 refer to a single diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

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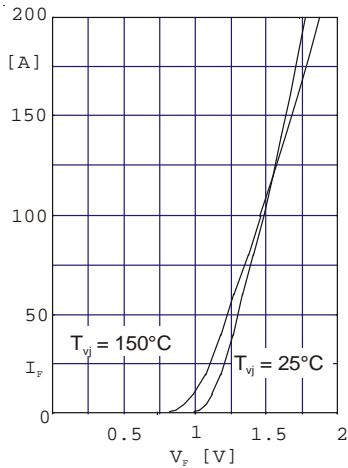


Fig. 1 Forward current versus voltage drop per diode

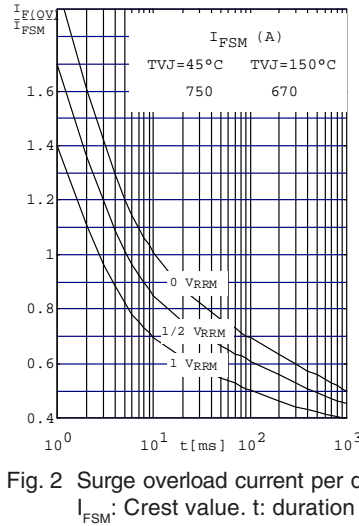


Fig. 2 Surge overload current per diode I_{FSM} : Crest value. t: duration

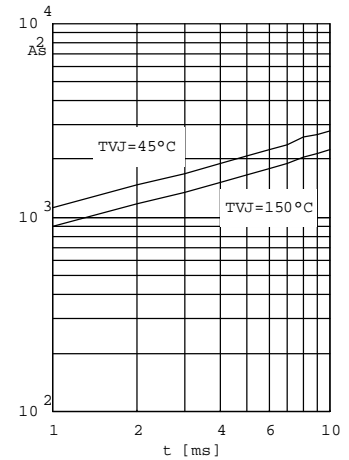


Fig. 3 I^2dt versus time (1-10ms) per diode or thyristor

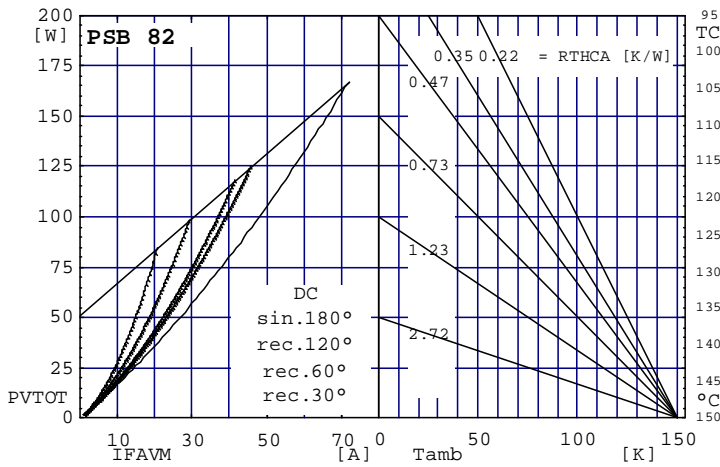


Fig. 4 Power dissipation vs. direct output current and ambient temperature

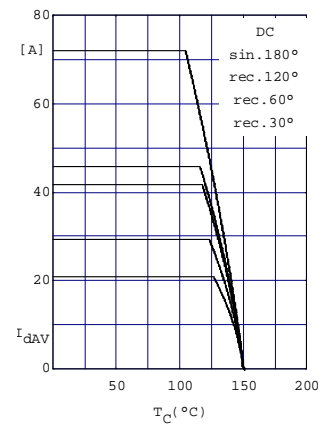


Fig. 5 Maximum forward current at case temperature

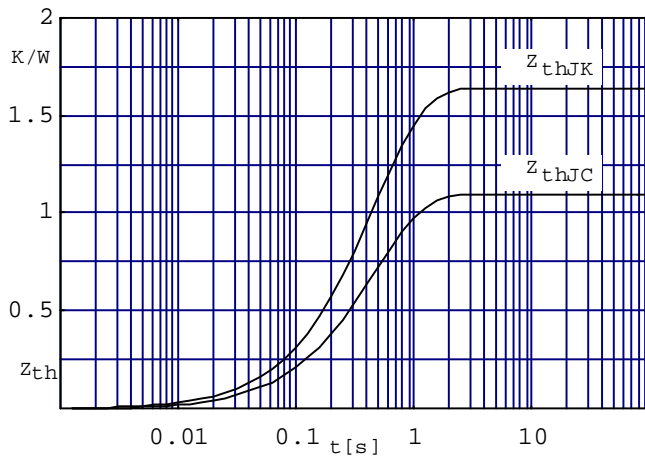


Fig. 6 Transient thermal impedance per diode or thyristor, calculated